

MMBD1501(A) THRU MMBD1505(A)

**High Conductance
Low Leakage Diode
350mW**

Features

- Low Leakage
- Surface Mount Package Ideally Suited for Automatic Insertion
- 150°C Junction Temperature
- High Conductance

Mechanical Data

- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0 and MSL Rating 1
- Polarity: See Diagram
- Weight: 0.008 grams (approx.)

Maximum Ratings @ 25°C Unless Otherwise Specified

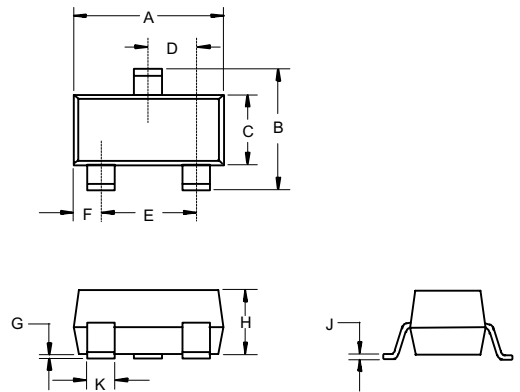
Characteristic	Symbol	Value	Unit
Working Inverse Voltage	V_{IV}	180	V
DC Forward Current	I_F	600	mA
Average Rectified Current	I_o	200	mA
Recurrent Peak Forward Current	i_f	700	mA
Peak Forward Surge Current @ $t=1.0s$ @ $t=1.0ms$	$i_{f(surge)}$	1.0 2.0	A
Power Dissipation	P_d	350	mW
Thermal Resistance	R	357	°C/W
Operation & Storage Temp. Range	T_j, T_{STG}	-55 to +150	°C

Note: 1) These ratings are based on a max. junction temperature of 150 degrees C
 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operation

Electrical Characteristics @ 25°C Unless Otherwise Specified

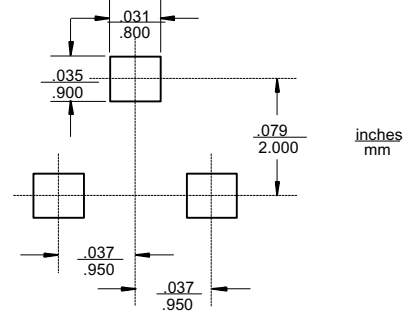
Charateristic	Symbol	Min	Max	Unit	Test Cond.
Breakdown Voltage	B_v	200		V	$I_R=5.0\mu A$
Forward Voltage Drop	V_F	620	750	mV	$I_F=1.0mA$
		720	850	mV	$I_F=10mA$
		800	950	mV	$I_F=50mA$
		0.83	1.1	V	$I_F=100mA$
		0.87	1.3	V	$I_F=200mA$
		0.9	1.5	V	$I_F=300mA$
Reverse Current	I_R	-----	10 5.0	nA uA	$V_R=180V$ $V_R=180V T_A=150^\circ C$
Junction Capacitance	C_j	-----	4	pF	$V_R=0V, f=1.0MHz$

SOT-23



DIM	DIMENSIONS				NOTE
	INCHES		MM		
A	.110	.120	2.80	3.04	
B	.083	.098	2.10	2.64	
C	.047	.055	1.20	1.40	
D	.035	.041	.89	1.03	
E	.070	.081	1.78	2.05	
F	.018	.024	.45	.60	
G	.0005	.0039	.013	.100	
H	.035	.044	.89	1.12	
J	.003	.007	.085	.180	
K	.015	.020	.37	.51	

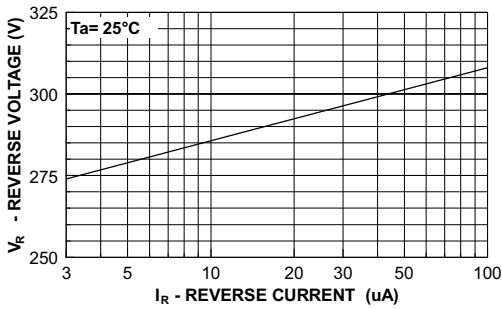
Suggested Solder Pad Layout



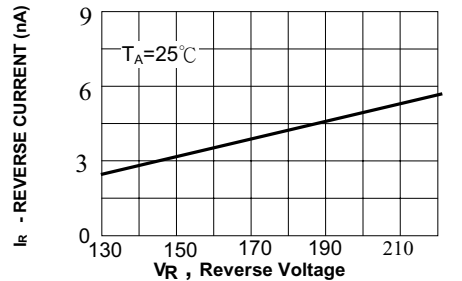
MMBD1501(A) thru MMBD1505(A)

TM

REVERSE VOLTAGE vs REVERSE CURRENT
BV - 3.0 to 100 μ A

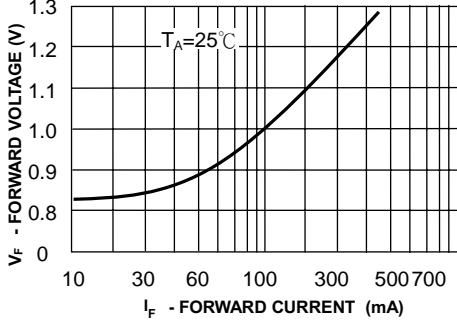


Reverse Current Vs Reverse Voltage
 I_R - 130 - 205 volts

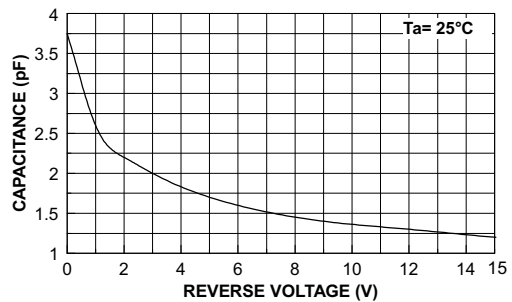


GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

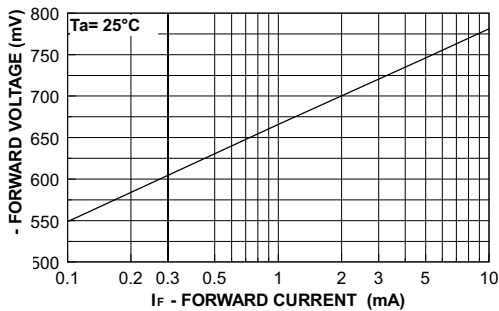
FORWARD VOLTAGE vs FORWARD CURRENT
VF - 10 to 800 mA



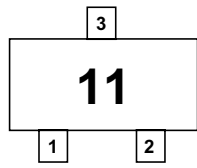
CAPACITANCE vs REVERSE VOLTAGE
VR - 0 to 15 V



FORWARD VOLTAGE vs FORWARD CURRENT
VF - 0.1 to 10 mA

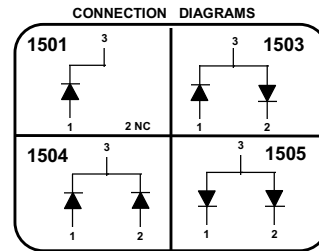


MMBD1501(A) thru MMBD1505(A)



MARKING

MMBD1501(A) 11/A11
MMBD1503(A) 13/A13
MMBD1504(A) 14/A14
MMBD1505(A) 15/A15



Ordering Information

Device	Packing
(Part Number)-TP	Tape&Reel;3Kpcs/Reel

■

■

■

■
